

Technical documentation



Support & ക training



SN74LVCH32373A

ZHCSLJ9E - OCTOBER 1998 - REVISED JULY 2020

具有三态输出的 SN74LVCH32373A 32 位透明 D 型锁存器

1 特性

- 德州仪器 (TI) Widebus+™ 系列产品 •
- 工作电压范围为 1.65V 至 3.6V •
- 输入电压高达 5.5V
- 电压为 3.3V 时, t_{pd} 最大值为 4.2ns
- VOLP(输出接地反弹)典型值 小于 0.8V (V_{CC} = 3.3V、T_A = 25°C 时)
- V_{OHV} (输出 V_{OH} 下冲) 典型值 大于 2V (V_{CC} = 3.3V、T_A = 25°C 时)
- Ioff 支持局部断电模式运行
- 支持混合模式信号运行
 - (5V 输入或输出电压,
 - 具有 3.3V V_{CC})
- 总线保持数据输入消除了对外部上拉/下拉电阻的需 求
- 闩锁性能超过 250mA, 符合 JESD 17 规范
- ESD 保护性能超过 JESD 22 规范要求
 - 2000V 人体放电模型 (A114-A)
 - 200V 机器放电模型 (A115-A)

2 应用

- 缓冲寄存器
- I/O 端口
- 双向总线驱动器
- 工作寄存器

3 说明

这款 32 位透明 D 型锁存器旨在 1.65V 至 3.6V V_{CC} 下 运行。

SN74LVCH32373A 特别适合于实现缓冲寄存器、I/O 端口、双向总线驱动器和工作寄存器。它可以用作四个 8 位锁存器、两个 16 位锁存器或一个 32 位锁存器。 在锁存器使能 (LE) 输入为高电平时, Q 输出将跟随数 据 (D) 输入。当 LE 为低电平时, Q 输出被锁存在 D 输入端设置的电平。

器件信息					
器件型号	封装 ⁽¹⁾	封装尺寸 (标称值)			
SN74LVCH32373AG KER	LFBGA-GKE	13.50mm × 5.00mm			
SN74LVCH32373AN MJR	LFBGA-NMJ	13.50mm × 5.00mm			

(1) 如需了解所有可用封装,请参阅数据表末尾的可订购产品附 录。



逻辑图





Table of Contents

1	特性1	
2	应用1	
3	说明1	
4	Revision History2	
5	Pin Configuration and Functions	
6	Specifications7	
	6.1 Absolute Maximum Ratings7	
	6.2 ESD Ratings7	
	6.3 Recommended Operating Conditions8	
	6.4 Thermal Information8	
	6.5 Electrical Characteristics9	
	6.6 Timing Requirements9	
	6.7 Switching Characteristics10	
	6.8 Operating Characteristics 10	
	6.9 Typical Characteristics10	
7	Detailed Description12	
	7.1 Overview12	
	7.2 Functional Block Diagram13	

_
3
5
6
~
О
6
8
8
8
q
~
9
9
9
9
9
a
9
9
Ĩ

4 Revision History

Changes from Revision D (March 2005) to Revision E (July 2020)	Page
• 全局更改为新的 TI 数据表格式	1
• 添加了"应用"列表、"器件信息"表和重要图形	1
Added maximum junction temperature	7
Added ESD Ratings section	7
Added Thermal Information section	8
Added Typical Characteristics section	
Added Detailed Description section	
Added Application and Implementation section	
Added Power Supply Recommendations section and Layout section	



5 Pin Configuration and Functions





Pin Functions

PIN		1/0	DESCRIPTION
NAME	NO.		DESCRIPTION
1Q2	A1	Output	Bank 1, Channel 2, Q Output
1Q4	B1	Output	Bank 1, Channel 4, Q Output
1Q6	C1	Output	Bank 1, Channel 6, Q Output
1Q8	D1	Output	Bank 1, Channel 8, Q Output
2Q2	E1	Output	Bank 2, Channel 2, Q Output
2Q4	F1	Output	Bank 2, Channel 4, Q Output
2Q6	G1	Output	Bank 2, Channel 6, Q Output

Copyright © 2021 Texas Instruments Incorporated



Pin Functions (continued)

PIN		1/0	DESCRIPTION	
NAME	NO.		DESCRIPTION	
2Q7	H1	Output	Bank 2, Channel 8, Q Output	
3Q2	J1	Output	Bank 3, Channel 2, Q Output	
3Q4	K1	Output	Bank 3, Channel 4, Q Output	
3Q6	L1	Output	Bank 3, Channel 6, Q Output	
3Q8	M1	Output	Bank 3, Channel 8, Q Output	
4Q2	N1	Output	Bank 4, Channel 2, Q Output	
4Q4	P1	Output	Bank 4, Channel 4, Q Output	
4Q6	R1	Output	Bank 4, Channel 6, Q Output	
4Q7	T1	Output	Bank 4, Channel 8, Q Output	
1Q1	A2	Output	Bank 1, Channel 1, Q Output	
1Q3	B2	Output	Bank 1, Channel 3, Q Output	
1Q5	C2	Output	Bank 1, Channel 5, Q Output	
1Q7	D2	Output	Bank 1, Channel 7, Q Output	
2Q1	E2	Output	Bank 2, Channel 1, Q Output	
2Q3	F2	Output	Bank 2, Channel 3, Q Output	
2Q5	G2	Output	Bank 2, Channel 5, Q Output	
2Q8	H2	Output	Bank 2, Channel 7, Q Output	
3Q1	J2	Output	Bank 3, Channel 1, Q Output	
3Q3	K2	Output	Bank 3, Channel 3, Q Output	
3Q5	L2	Output	Bank 3, Channel 5, Q Output	
3Q7	M2	Output	ank 3, Channel 7, Q Output	
4Q1	N2	Output	Bank 4, Channel 1, Q Output	
4Q3	P2	Output	Bank 4, Channel 3, Q Output	
4Q5	R2	Output	Bank 4, Channel 5, Q Output	
4Q8	T2	Output	Bank 4, Channel 7, Q Output	
1 OE	A3	Input	Bank 1, Output Enable, Active Low	
GND	B3	_	Ground	
V _{CC}	C3	_	Positive Supply	
GND	D3	_	Ground	
GND	E3	_	Ground	
V _{CC}	F3	_	Positive Supply	
GND	G3	_	Ground	
2 OE	НЗ	Input	Bank 2, Output Enable, Active Low	
3 OE	J3	Input	Bank 3, Output Enable, Active Low	
GND	К3	_	Ground	
V _{CC}	L3	_	Positive Supply	
GND	M3	_	Ground	
GND	N3	_	Ground	
V _{CC}	P3	Input	Positive Supply	
GND	R3	· · ·	Ground	
4 OE	Т3	Input	Bank 4, Output Enable, Active Low	
1LE	A4	Input	Bank 1, Latch Enable, Active Low	
GND	B4	_	Ground	
Vcc	C4	_	Positive Supply	



Pin Functions (continued)

PIN		1/0	DESCRIPTION
NAME	NO.		DESCRIPTION
GND	D4		Ground
GND	E4	_	Ground
V _{CC}	F4		Positive Supply
GND	G4	_	Ground
2LE	H4	Input	Bank 2, Latch Enable, Active Low
3LE	J4	Input	Bank 3, Latch Enable, Active Low
GND	K4		Ground
V _{CC}	L4	_	Positive Supply
GND	M4	_	Ground
GND	N4	_	Ground
V _{CC}	P4	_	Positive Supply
GND	R4	_	Ground
4LE	T4	Input	Bank 4, Latch Enable, Active Low
1D1	A5	Input	Bank 1, Channel 1, Data Input
1D3	B5	Input	Bank 1, Channel 3, Data Input
1D5	C5	Input	Bank 1, Channel 5, Data Input
1D7	D5	Input	Bank 1, Channel 7, Data Input
2D1	E5	Input	Bank 2, Channel 1, Data Input
2D3	F5	Input	Bank 2, Channel 3, Data Input
2D5	G5	Input	Bank 2, Channel 5, Data Input
2D8	H5	Input	Bank 2, Channel 8, Data Input
3D1	J5	Input	Bank 3, Channel 1, Data Input
3D3	K5	Input	Bank 3, Channel 3, Data Input
3D5	L5	Input	Bank 3, Channel 5, Data Input
3D7	M5	Input	Bank 3, Channel 7, Data Input
4D1	N5	Input	Bank 4, Channel 1, Data Input
4D3	P5	Input	Bank 4, Channel 3, Data Input
4D5	R5	Input	Bank 4, Channel 5, Data Input
4D8	T5	Input	Bank 4, Channel 8, Data Input
1D2	A6	Input	Bank 1, Channel 2, Data Input
1D4	B6	Input	Bank 1, Channel 4, Data Input
1D6	C6	Input	Bank 1, Channel 6, Data Input
1D8	D6	Input	Bank 1, Channel 8, Data Input
2D2	E6	Input	Bank 2, Channel 2, Data Input
2D4	F6	Input	Bank 2, Channel 4, Data Input
2D6	G6	Input	Bank 2, Channel 6, Data Input
2D7	H6	Input	Bank 2, Channel 7, Data Input
3D2	J6	Input	Bank 3, Channel 2, Data Input
3D4	K6	Input	Bank 3, Channel 4, Data Input
3D6	L6	Input	Bank 3, Channel 6, Data Input
3D8	M6	Input	Bank 3, Channel 8, Data Input
4D2	N6	Input	Bank 4, Channel 2, Data Input
4D4	P6	Input	Bank 4, Channel 4, Data Input
4D6	R6	Input	Bank 4, Channel 6, Data Input



Pin Functions (continued)

PIN		1/0	DESCRIPTION		
NAME	NO.	"0	BESCHIFTION		
4D7	T6	Input	Bank 4, Channel 7, Data Input		



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage range		- 0.5	6.5	V
VI	Input voltage range ⁽²⁾		- 0.5	6.5	V
Vo	Voltage range applied to any output in the high-impeda	nce or power-off state ⁽²⁾	- 0.5	6.5	V
Vo	Voltage range applied to any output in the high or low s	tate ^{(2) (3)}	- 0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V ₁ < 0		- 50	mA
I _{OK}	Output clamp current	V _O < 0		- 50	mA
I _O	Continuous output current			±50	mA
	Continuous current through each V_{CC} or GND			±100	mA
TJ	Junction temperature			150	°C
T _{stg}	Storage temperature range		- 65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

(3) The value of V_{CC} is provided in the recommended operating conditions table.

6.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V	Supply voltage	Operating	1.65	3.6	V
V CC		Data retention only	1.5		v
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		
VIH	High-level input voltage	V _{CC} = 2.3 V to 2.7 V	1.7		V
		V _{CC} = 2.7 V to 3.6 V	2		
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}	
VIL	Low-level input voltage	V _{CC} = 2.3 V to 2.7 V		0.7	V
		V _{CC} = 2.7 V to 3.6 V		0.8	
VI	Input voltage	·	0	5.5	V
V.	Output voltage	High or low state	0	V _{CC}	V
VO		3-state	0	5.5	
	High-level output current	V _{CC} = 1.65 V		- 4	mA
		V _{CC} = 2.3 V		- 8	
юн		V _{CC} = 2.7 V		- 12	
		V _{CC} = 3 V		- 24	
		V _{CC} = 1.65 V		4	
		V _{CC} = 2.3 V		8	mA
IOL	Low-level output current	V _{CC} = 2.7 V		12	
		V _{CC} = 3 V		24	
Δ t/ Δ v	Input transition rise or fall rate			10	ns/V
T _A	Operating free-air temperature		- 40	85	°C

6.4 Thermal Information

		SN74LVC		
	THERMAL METRIC ⁽¹⁾	GKE	UNIT	
		96 PINS	96 PINS	
R _{0 JA}	Junction-to-ambient thermal resistance	44.4	26.7	°C/W
R _{0 JC(top)}	Junction-to-case (top) thermal resistance	26.1	14.4	°C/W
R _{0 JB}	Junction-to-board thermal resistance	23.9	10.7	°C/W
ΨJT	Junction-to-top characterization parameter	1.3	1.3	°C/W
ψ _{JB}	Junction-to-board characterization parameter	23.8	10.5	°C/W
R _{0 JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC package thermal metrics application report.



6.5 Electrical Characteristics

PARAMETER	TEST C	ONDITIONS	Vcc	MIN	TYP ⁽¹⁾ MAX	UNIT	
	I _{OH} = -100 μA		1.65 V to 3.6 V	V _{CC} - 0.2			
	I _{OH} = -4 mA		1.65 V	1.2			
Maria	I _{OH} = -8 mA		2.3 V	1.7		V	
⊻он	$1 - 12 m^{1}$		2.7 V	v			
	$I_{OH} = 12 \text{ mA}$		3 V	2.4			
	I _{OH} = - 24 mA		3 V	2.2			
	I _{OL} = 100 μ A		1.65 V to 3.6 V		0.2		
	I _{OL} = 4 mA		1.65 V		0.45		
V _{OL}	I _{OL} = 8 mA		2.3 V		0.7	V	
	I _{OL} = 12 mA		2.7 V				
	I _{OL} = 24 mA		3 V		0.55		
l _l	V _I = 0 to 5.5 V		3.6 V		±5	μA	
	V _I = 0.58 V		1.65 V	25			
	V _I = 1.07 V		1.05 V	- 25			
	V _I = 0.7 V		2.2.1/	45			
I _{I(hold)}	V _I = 1.7 V		2.3 V	- 45		μA	
	V _I = 0.8 V		2.1/	75			
	V ₁ = 2 V		SV	- 75			
	$V_1 = 0$ to 3.6 $V^{(2)}$		3.6 V		±500		
I _{off}	$V_{\rm I}$ or $V_{\rm O}$ = 5.5 V		0		±10	μ Α	
I _{OZ}	V _O = 0 to 5.5 V		3.6 V		±10	μ Α	
	V _I = V _{CC} or GND		2.01/		40	•	
ICC	$3.6~\textrm{V} \leqslant \textrm{V}_\textrm{I} \leqslant 5.5~\textrm{V}^{(3)}$	10 - 0	3.0 V		40	μΑ	
∆ I _{CC}	One input at V _{CC} - 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V		μA		
C _i	V _I = V _{CC} or GND		3.3 V		5	pF	
Co	$V_0 = V_{CC}$ or GND		3.3 V		6.5	pF	

over recommended operating free-air temperature range (unless otherwise noted)

(1) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

(2) This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

(3) This applies in the disabled state only.

6.6 Timing Requirements

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		V _{CC} = ± 0.1	1.8 V 5 V	V _{CC} = 2 ± 0.2	2.5 V 2 V	V _{CC} = 2	2.7 V	V _{CC} = : ± 0.3	V _{CC} = 3.3 V ± 0.3 V	
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _w	Pulse duration, LE high	(1)		(1)		3.3		3.3		ns
t _{su}	Setup time, data before LE ↓	(1)		(1)		1.7		1.7		ns
t _h	Hold time, data after LE ↓	(1)		(1)		1.2		1.2		ns

(1) This information was not available at the time of publication.



6.7 Switching Characteristics

PARAMETER			V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
	(INFOT)		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t .	D	Q	(1)	(1)	(1)	(1)		4.9	1.6	4.2	nc
Чрd	LE		(1)	(1)	(1)	(1)		5.3	2.1	4.6	115
t _{en}	ŌĒ	Q	(1)	(1)	(1)	(1)		5.7	1.3	4.7	ns
t _{dis}	ŌE	Q	(1)	(1)	(1)	(1)		6.3	2.5	5.9	ns

over operating free-air temperature range (unless otherwise noted)

(1) This information was not available at the time of publication.

6.8 Operating Characteristics

T_A = 25°C

	DADAMETED		TEST	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	
	r Alvame i Elv	CONDITIONS	TYP TYP		TYP	UNIT	
C	Power dissipation capacitance	Outputs enabled	f - 10 MHz	(1)	(1)	39	nE
Cpd	per latch	Outputs disabled		(1)	(1)	6	pi

(1) This information was not available at the time of publication.

6.9 Typical Characteristics





VI

Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

	IN	PUTS	N	V	•	-	V
VCC	VI	t _r /t _f	VM	VLOAD	CL	КL	ν _Δ
$1.8~V\pm0.15~V$	V _{CC}	≤2 ns	V _{CC} /2	$2 \times V_{CC}$	30 pF	1 k Ω	0.15 V
$\textbf{2.5 V} \pm \textbf{0.2 V}$	V _{CC}	≤2 ns	V _{CC} /2	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V
2.7 V	2.7 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
3.3 V \pm 0.3 V	2.7 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V





VOLTAGE WAVEFORMS PROPAGATION DELAY TIMES INVERTING AND NONINVERTING OUTPUTS

VM

NOTES: A. C_L includes probe and jig capacitance.

Output

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control. C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω .

VOH

 V_{OL}

D. The outputs are measured one at a time, with one transition per measurement.

٧м

- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd}.
- H. All parameters and waveforms are not applicable to all devices.

图 7-1. Load Circuit and Voltage Waveforms

11



7 Detailed Description

7.1 Overview

The SN74LVCH32373A is a 32-bit transparent D-type latch that is designed for 1.65-V to 3.6-V V_{CC} operation.

A buffered output-enable (\overline{OE}) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components.

OE does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pull-up resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry holds unused or undriven inputs at a valid logic state. Use of pull-up or pull-down resistors with the bus-hold circuitry is not recommended.

Latches are arranged in banks of 8, with each bank having a separate latch enable (LE) and output enable (\overline{OE}) associated with it, as shown in the functional block diagram below.

When the latch enable pin for a bank is asserted (HIGH), the outputs will follow the data inputs.

When the latch enable pin for a bank is de-asserted (LOW), the outputs will continue to hold the valid input value at the time of switching.

When the output enable pin is asserted (LOW), the output is active.

When the output enable pin is de-asserted (HIGH), the output is disabled (high impedance). This does not affect the latch operation.



7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Standard CMOS Inputs

Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance to ground given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using ohm's law ($R = V \div I$).

Signals applied to the inputs need to have fast edge rates, as defined by $\Delta t / \Delta v$ in the *Recommended Oeprating Conditions* to avoid excessive current consumption and oscillations. If a slow or noisy input signal is required, a device with a Schmitt-trigger input should be used to condition the input signal prior to the standard CMOS input.

7.3.2 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

7.3.3 Partial Power Down (I_{off})

The inputs and outputs for this device enter a high-impedance state when the device is powered down, inhibiting current backflow into the device. The maximum leakage into or out of any input or output pin on the device is specified by I_{off} in the *Electrical Characteristics*.



7.3.4 Over-voltage Tolerant Inputs

Input signals to this device can be driven above the supply voltage so long as they remain below the maximum input voltage value specified in the *Recommended Operating Conditions*.

7.3.5 Clamp Diode Structure

The inputs and outputs to this device have negative clamping diodes only as depicted in 图 7-1.

CAUTION

Voltages beyond the values specified in the Absolute Maximum Ratings table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.



图 7-1. Electrical Placement of Clamping Diodes for Each Input and Output

7.3.6 Bus-Hold Data Inputs

Each data input (D) on this device includes a weak latch that maintains a valid logic level on the input. The state of these latches is unknown at startup and remains unknown until the input has been forced to a valid high or low state. After data has been sent through a channel, the latch then maintains the previous state on the input if the line is left floating. It is not recommended to use pull-up or pull-down resistors together with a bus-hold input, as it may cause undefined inputs to occur which can lead to excessive current consumption.

Bus-hold data inputs prevent floating inputs on this device. The Implications of Slow or Floating CMOS Inputs application report explains the problems associated with leaving CMOS inputs floating. These latches remain active at all times, independent of all control signals such as direction control or output enable. The Bus-Hold Circuit application report has additional details regarding bus-hold inputs.



图 7-2. Bus-Hold circuit block diagram representation



7.4 Device Functional Modes



图 7-3. Logic Diagram (Positive Logic)



8 Application and Implementation

Note

以下应用部分的信息不属于 TI 组件规范, TI 不担保其准确性和完整性。客户应负责确定 TI 组件是否适用于其应用。客户应验证并测试其设计,以确保系统功能。

8.1 Application Information

In this application, the SN74LVCH32373A 32-bit D-type latch with bus-hold inputs is used to control a 24-bit bus.

8.2 Typical Application



图 8-1. Simplified schematic for typical application

8.2.1 Design Requirements

- · All signals in the system operate at the same voltage within the recommended operating range of the device
- Inputs can be disconnected or placed into the high-impedance state; bus-hold circuitry will maintain the last known state at the input
- · Outputs must remain active at all times to prevent the bus from floating

8.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics*.

The supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74LVCH32373A plus the maximum supply current, I_{CC} , listed in the *Electrical Characteristics*. The logic device can only source or sink as much current as it is provided at the supply and ground pins, respectively. Be sure not to exceed the maximum total current through GND or V_{CC} listed in the *Absolute Maximum Ratings*.



The SN74LVCH32373A can drive a load with a total capacitance less than or equal to 50 pF connected to a high-impedance CMOS input while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed 70 pF.

Total power consumption can be calculated using the information provided in CMOS Power Consumption and C_{pd} Calculation.

Thermal increase can be calculated using the information provided in Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices.

CAUTION

The maximum junction temperature, $T_J(max)$ listed in the *Absolute Maximum Ratings*, is an *additional limitation* to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

8.2.1.2 Input Considerations

Unused inputs must be terminated to either V_{CC} or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74LVCH32373A, as specified in the *Electrical Characteristics*, and the desired input transition rate. A 10-k Ω resistor value is often used due to these factors.

The SN74LVCH32373A has standard CMOS inputs, so input signal edge rates cannot be slow. Slow input edge rates can cause oscillations and damaging shoot-through current. The recommended rates are defined in the *Recommended Operating Conditions*.

Refer to the *Feature Description* for additional information regarding the inputs for this device.

8.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. Similarly, the ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*. The plots in $\cancel{8}$ 8-2 and $\cancel{8}$ 8-3 provide a typical relationship between output voltage and current for this device.

Unused outputs can be left floating.

Refer to *Feature Description* for additional information regarding the outputs for this device.

8.2.1.4 Timing Considerations

The SN74LVCH32373A is a latched device. As such, it requires special timing considerations to ensure normal operation.

Primary timing factors to consider:

- Pulse duration: ensure that the triggering event duration is larger than the minimum pulse duration, as defined in the *Timing Requirements*.
- Setup time: ensure that the data has changed at least one setup time prior to the triggering event, as defined in the *Timing Requirements*.
- Hold time: ensure that the data remains in the desired state at least one hold time after the triggering event, as defined in the *Timing Requirements*.

8.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from each supply pin (V_{CC}) to a nearby GND pin. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. For BGA type



packages, these capacitors are often placed on the back of the board to minimize trace length. Adding one capacitor per supply pin is recommended.

- 2. Ensure the capacitive load at the output is ≤ 70 pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74LVCH32373A to the receiving device.
- Ensure the resistive load at the output is larger than (V_{CC} / 50 mA) Ω. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.
- 4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, CMOS Power Consumption and Cpd Calculation. In multi-channel high-speed applications, it is possible to reach the thermal limits of the device without violating any other absolute maximum ratings.



8.2.3 Application Curves

9 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.022- μ F capacitor at each supply pin is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The bypass capacitor should be installed as close to the power terminal as possible for best results. With BGA packages, this often means putting the capacitors on the back of the board.

10 Layout

10.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only 24 channels of a 32-channel D-type latch are used. Pins with bus-hold circuitry (xDy) are automatically held in a valid state and can be left unconnected without the input voltage floating. Other inputs, such as the xLE and x \overline{OE} must be terminated at either ground or V_{CC} to prevent floating. Generally, the inputs are tied to GND or V_{CC}, whichever makes more sense for the logic function or is more convenient.

It is not recommended to use pull-up or pull-down resistors with bus-hold inputs.



10.2 Layout Example



图 10-1. BGA layout examples

11 Device and Documentation Support

11.1 Documentation Support

11.1.1 Related Documentation

For related documentation see the following:

- CMOS Power Consumption and CPD Calculation
- Designing with Logic

11.2 Support Resources

TI E2E^M support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

11.3 Trademarks

Widebus+[™] is a trademark of Texas Instruments. TI E2E[™] is a trademark of Texas Instruments.

所有商标均为其各自所有者的财产。

11.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.5 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Copyright © 2021 Texas Instruments Incorporated



PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVCH32373ANMJR	ACTIVE	NFBGA	NMJ	96	1000	RoHS & Green	SNAGCU	Level-3-260C-168 HR	-40 to 85	29TW	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

Texas Instruments

www.ti.com

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVCH32373ANMJR	NFBGA	NMJ	96	1000	330.0	24.4	5.85	13.85	1.8	8.0	24.0	Q1



www.ti.com

PACKAGE MATERIALS INFORMATION

26-May-2021



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVCH32373ANMJR	NFBGA	NMJ	96	1000	336.6	336.6	41.3

NMJ0096A

PACKAGE OUTLINE

NFBGA - 1.4 mm max height

PLASTIC BALL GRID ARRAY



- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



NMJ0096A

EXAMPLE BOARD LAYOUT

NFBGA - 1.4 mm max height

PLASTIC BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. Refer to Texas Instruments Literature number SNVA009 (www.ti.com/lit/snva009).



NMJ0096A

EXAMPLE STENCIL DESIGN

NFBGA - 1.4 mm max height

PLASTIC BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



重要声明和免责声明

TI"按原样"提供技术和可靠性数据(包括数据表)、设计资源(包括参考设计)、应用或其他设计建议、网络工具、安全信息和其他资源, 不保证没有瑕疵且不做出任何明示或暗示的担保,包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担 保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任:(1) 针对您的应用选择合适的 TI 产品,(2) 设计、验 证并测试您的应用,(3) 确保您的应用满足相应标准以及任何其他功能安全、信息安全、监管或其他要求。

这些资源如有变更,恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的应用。严禁对这些资源进行其他复制或展示。 您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成的任何索赔、损害、成 本、损失和债务,TI 对此概不负责。

TI 提供的产品受 TI 的销售条款或 ti.com 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

邮寄地址:Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2021,德州仪器 (TI) 公司